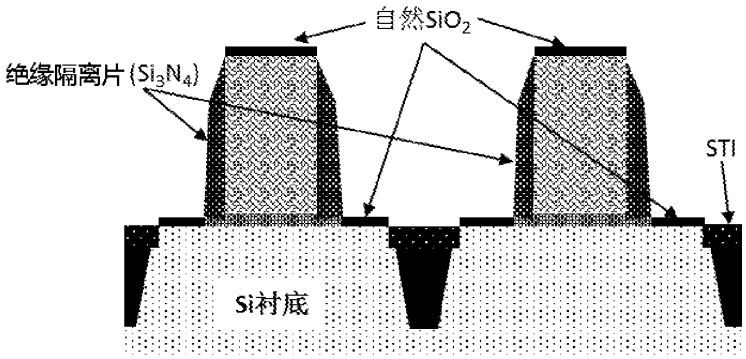

图 1a

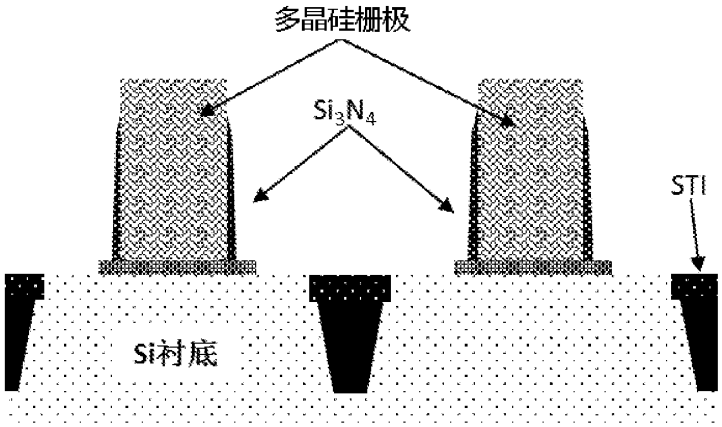

图 1b

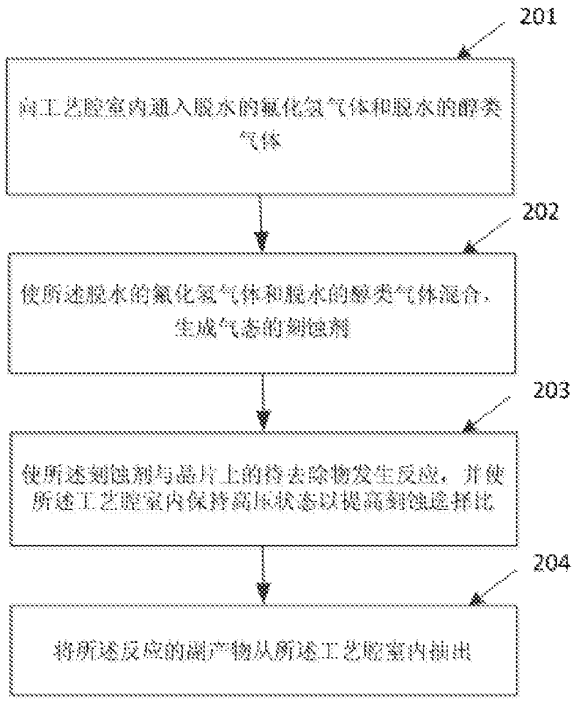
201
向工艺腔室内通入脱水的氟化氢气体和脱水的醇类气体
202
使所述脱水的氟化氢气体和脱水的醇类气体混合，生成气态的刻蚀剂
203
使所述刻蚀剂与晶片上的待去除物发生反应，并使所述工艺腔室内保持高压状态以提高刻蚀选择比
204
将所述反应的副产物从所述工艺腔室内抽出

图 2

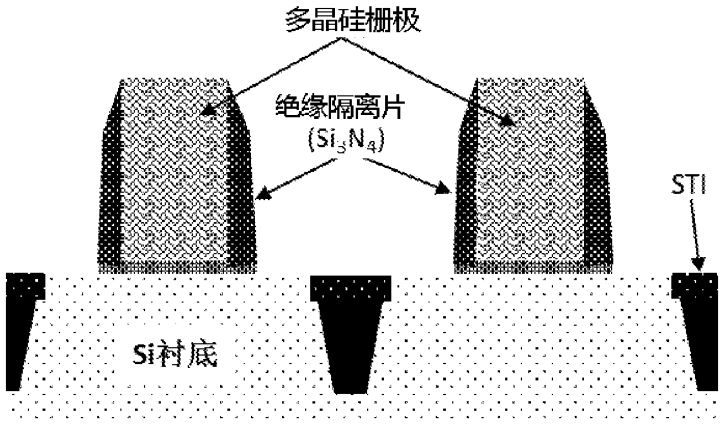
多晶硅栅极
绝缘隔离片
(Si_3N_4)
STI
Si衬底

图 3

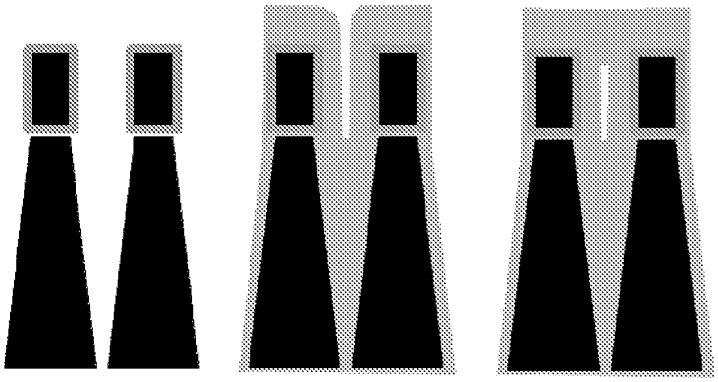

图 4a 图 4b 图 4c

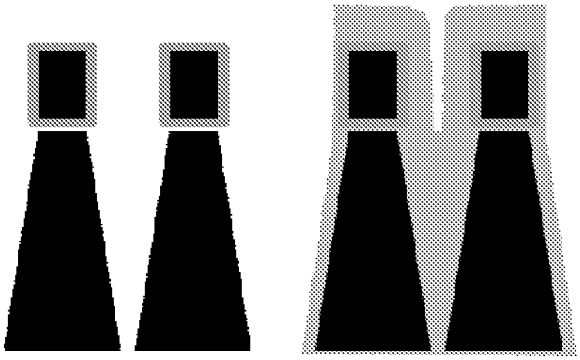

图 5a 图 5b

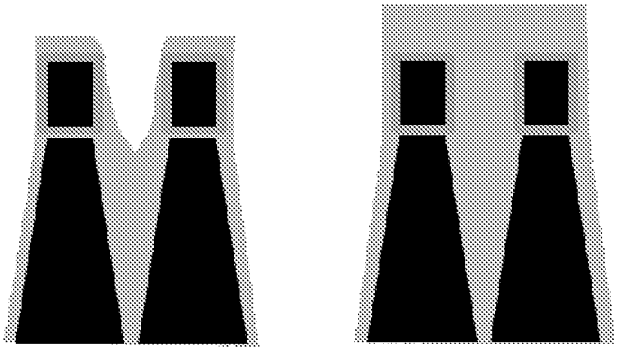

图 5c 图 5d

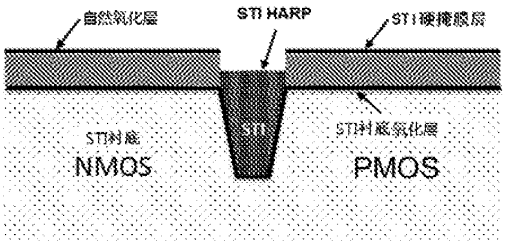

图 6a

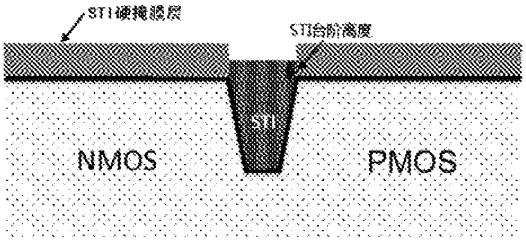

图 6b

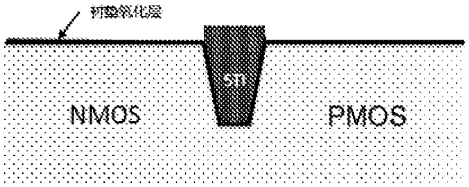

图 7a

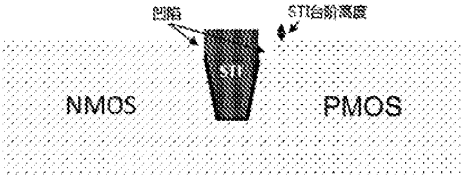

图 7b

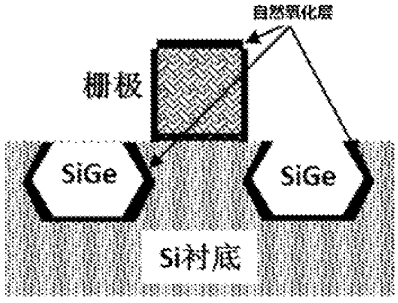

图 8a

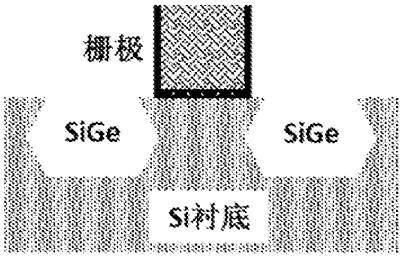

图 8b

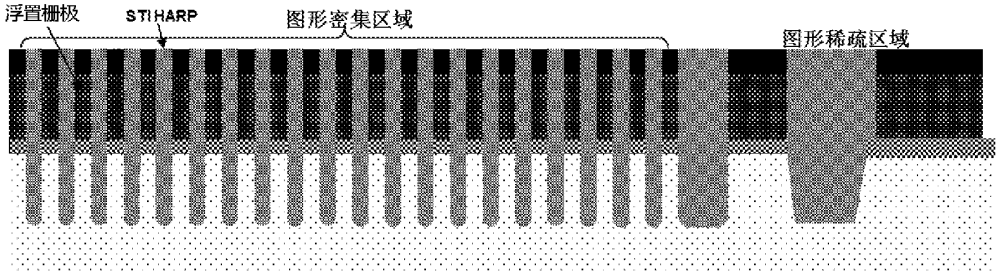

图 9a

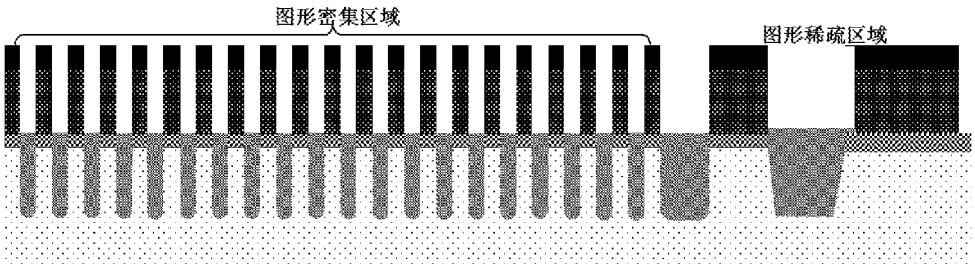

图 9b